



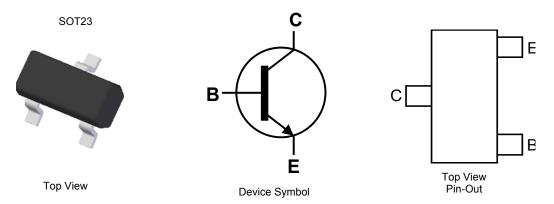
40V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: MMBT4403
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT23
- Case material: molded Plastic "Green" Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ^(G)
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT4401-7-F	AEC-Q101	K2X	7	8	3,000
MMBT4401-13-F	AEC-Q101	K2X	13	8	10,000
MMBT4401Q-13-F	Automotive	K2X	13	8	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

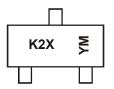
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K2X = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: A = 2013) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2010	20	011	2012	2	013	2014	1	2015	2016		2017
Code	Х		Y	Z		А	В		С	D		E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	c c	2	4	5	6	7	8	9	0	Ν	р



Absolute Maximum Ratings (@T_A = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	Ι _C	600	mA
Peak Collector Current	I _{CM}	1	А
Peak Base Current	I _{BM}	200	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	Б	310	mW	
Power Dissipation	(Note 7) P _D		350	11177	
Thermal Desistance Junction to Ambient	(Note 6)	P	403	0000	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	357	°C/W	
Thermal Resistance, Junction to Leads (Note 8)		R _{θJL}	350	°C/W	
Operating and Storage Temperature Range	T _J ,T _{STG}	-55 to +150	°C		

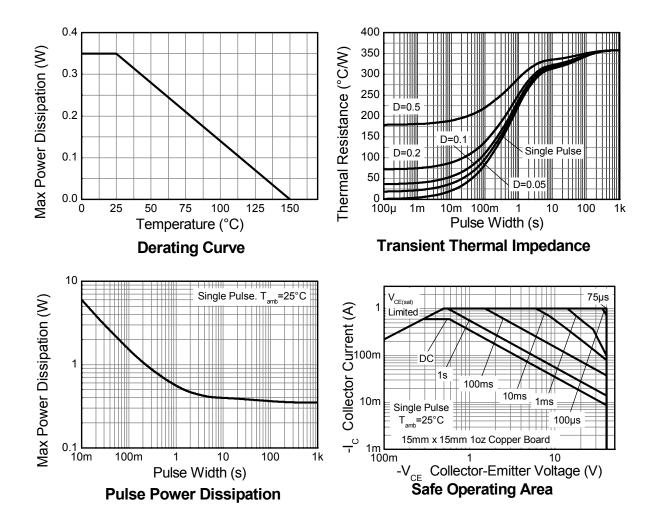
ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air To a device module of minimum recommended by layout 102 copper that is conditions whilst operating in a steady-state.
 Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the leads).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





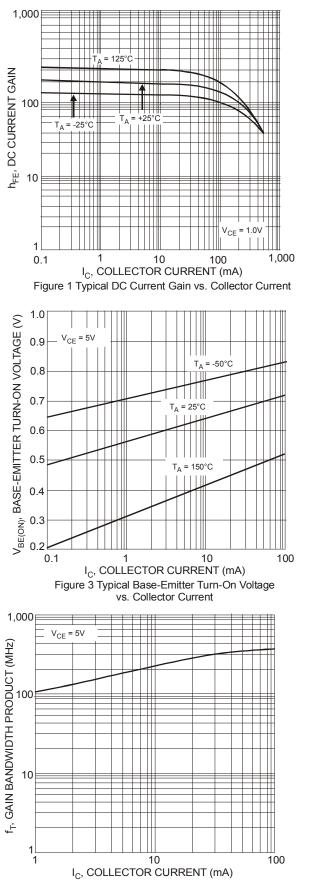
Electrical Characteristics (@T_A = +25°C unless otherwise specified)

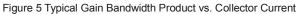
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage(Note 10)	BV _{CEO}	40	_	V	I _C = 10.0mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	_	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CEX}	_	100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
Base Cutoff Current	I _{BL}	_	100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
ON CHARACTERISTICS (Note 10)			•		
DC Current Gain	h _{FE}	20 40 80 100 40	 300	_	$I_{C} = 100 \mu A, V_{CE} = 1.0V$ $I_{C} = 1.0mA, V_{CE} = 1.0V$ $I_{C} = 10mA, V_{CE} = 1.0V$ $I_{C} = 150mA, V_{CE} = 1.0V$ $I_{C} = 500mA, V_{CE} = 2.0V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.40 0.75	v	$I_{C} = 150 \text{mA}, I_{B} = 15 \text{mA}$ $I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.75	0.95 1.2	V	I_{C} = 150mA, I_{B} = 15mA I_{C} = 500mA, I_{B} = 50mA
SMALL SIGNAL CHARACTERISTICS			1	T	I
Output Capacitance	C _{cb}		6.5	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{eb}		30	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1.0	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10⁻⁴	V _{CE} = 10V, I _C = 1.0mA,
Small Signal Current Gain	h _{fe}	40	500	—	f = 1.0kHz
Output Admittance	h _{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f _T	250	—	MHz	V_{CE} = 10V, I _C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d		15	ns	V _{CC} = 30V, I _C = 150mA,
Rise Time	tr	_	20	ns	V _{BE(off)} = 2.0V, I _{B1} = 15mA
Storage Time	ts		225	ns	V _{CC} = 30V, I _C = 150mA,
Fall Time	t _f		30	ns	$I_{B1} = -I_{B2} = 15 \text{mA}$

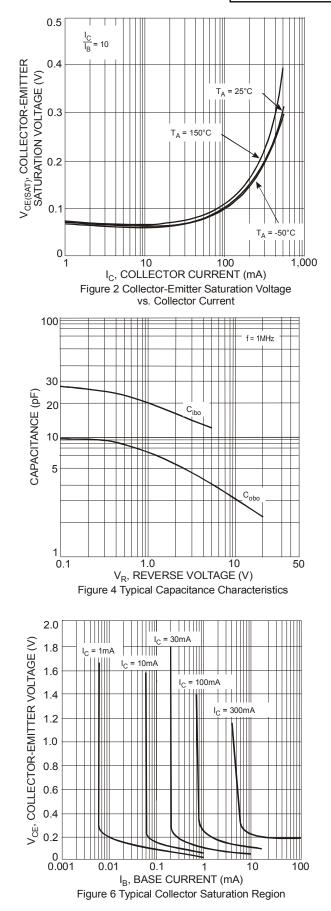
Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.







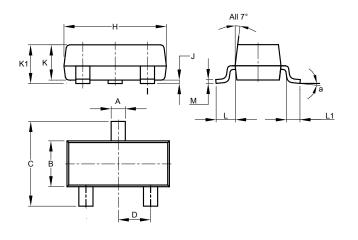






Package Outline Dimensions

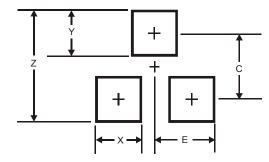
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а		8°					
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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